



PJSD05MLFN2

ESD PROTECTION DIODES

The PJSD05MLFN2 is designed to protect voltage sensitive components from ESD. Excellent clamping capability, low leakage, and fast response time provide best in class protection on designs that are exposed to ESD.

VOLTAGE 5 Volts **POWER** 90 Watts

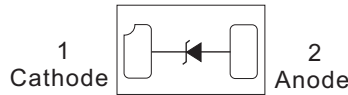
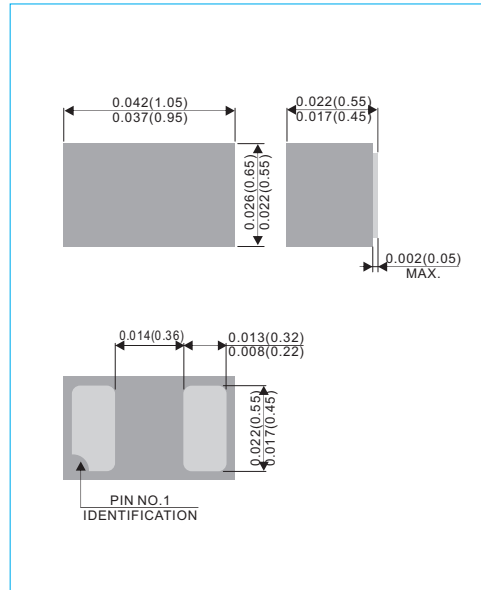
DFN 2L Unit : inch(mm)

FEATURES

- Low leakage
- Lead free in compliance with EU RoHS2.0 (2011/65/EU & 2015/865/EU directive)
- Green molding compound as per IEC61249 Std. . (Halogen Free)
- IEC61000-4-2 Level 4 ESD Protection
- IEC61000-4-4 Level 4 EFT Protection 80A ($t_p=5/50ns$)

MECHANICAL DATA

- Case: DFN 2L, Molded Plastic
- Terminals: Solderable per MIL-STD-750, Method 2026
- Polarity: Color band cathode
- Weight: 0.00004 ounces, 0.0011grams



MAXIMUM RATINGS

Rating	Symbol	Value	Units
Peak Power Dissipation 8/20 Surge Pulse	P_{PM}	90	W
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 to +150	°C

ELECTRICAL CHARACTERISTICS

($T_A=25^\circ\text{C}$ UNLESS OTHERWISE NOTED, $V_f=0.9\text{V Max.}@I_f=10\text{mA}$)

Device	$V_{RWM}(V)$	$I_R(\mu A)@V_{RWM}$	$V_{BR}(V)@I_T$ (Note 1)	I_T	$V_C(V)@MAX I_{PP}^+$	$I_{PP}(A)^+$	$P_{PK}(W)^+$	$C_J(pF)$	Marking Code
	Max	Max	Min	mA	Max	Max	Max	Typ	
PJSD05MLFN2	5.0	1.0	6.2	1.0	10	9	90	65	BR

NOTES:

*Other voltages available upon request

1. V_{BR} is measured with a pulse test current I_T at an ambient temperature of 25°C



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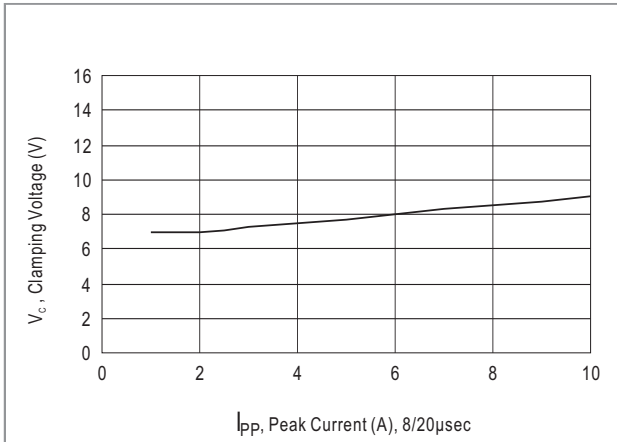


FIG. 1- Clamping Voltage

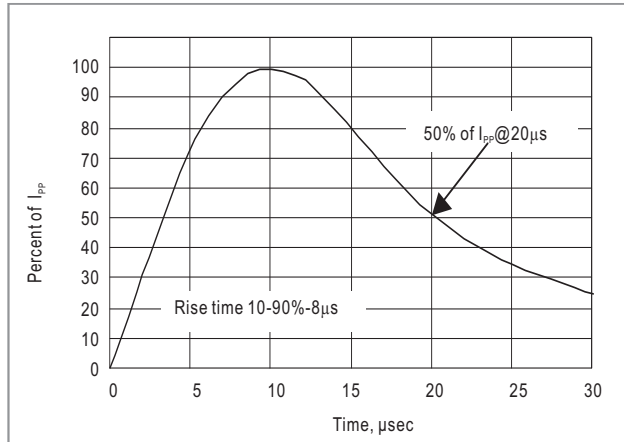


FIG. 2- Surge Pulse Waveform Definition

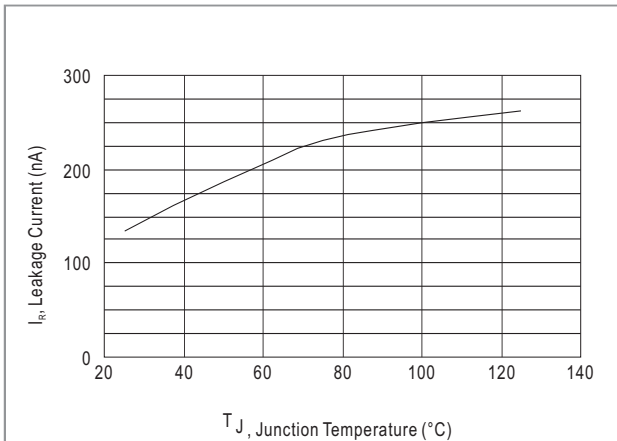


FIG. 3- Typical Reverse Characteristics

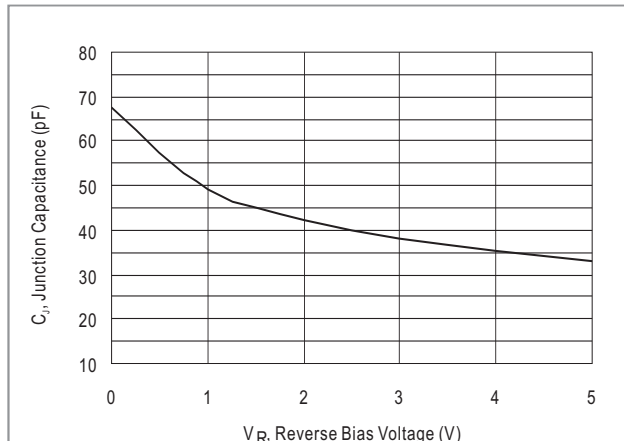


FIG. 4- Typical Junction Capacitance